

Meng Xiao

List of Publications by Year in descending order

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Version: 2024-02-01

10
papers

307
citations

1478505

6
h-index

1474206

9
g-index

10
all docs

10
docs citations

10
times ranked

371
citing authors

#	ARTICLE	IF	CITATIONS
1	High-Particle-Density YAG:Ce Phosphor Coating for High Power Laser Lighting. Journal of Electronic Packaging, Transactions of the ASME, 2020, 142, .	1.8	2
2	Abnormal Stranski-Krastanov Mode Growth of Green InGaN Quantum Dots: Morphology, Optical Properties, and Applications in Light-Emitting Devices. ACS Applied Materials & Interfaces, 2019, 11, 1228-1238.	8.0	51
3	Carrier lifetimes in polar InGaN-based LEDs. , 2018, , .		0
4	A Method to Obtain Auger Recombination Coefficient in an InGaN-Based Blue Light-Emitting Diode. Chinese Physics Letters, 2017, 34, 017301.	3.3	3
5	The influences of sputtered AlN buffer layer on AlInGaN based blue and near-ultraviolet light emitting diodes. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600714.	1.8	6
6	Influence of dislocation density on internal quantum efficiency of GaN-based semiconductors. AIP Advances, 2017, 7, 035321.	1.3	11
7	A Review on Experimental Measurements for Understanding Efficiency Droop in InGaN-Based Light-Emitting Diodes. Materials, 2017, 10, 1233.	2.9	37
8	Study on efficiency droop in InGaN/GaN light-emitting diodes based on differential carrier lifetime analysis. Applied Physics Letters, 2016, 108, .	3.3	40
9	An improved carrier rate model to evaluate internal quantum efficiency and analyze efficiency droop origin of InGaN based light-emitting diodes. Journal of Applied Physics, 2012, 112, 023107.	2.5	53
10	Understanding efficiency droop effect in InGaN/GaN multiple-quantum-well blue light-emitting diodes with different degree of carrier localization. Applied Physics Letters, 2010, 97, .	3.3	104